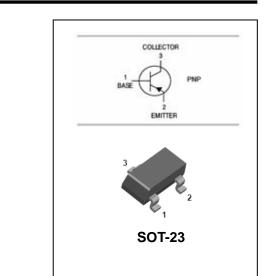
BL Galaxy Electrical

Silicon Epitaxial Planar Transistor

S8550

FEATURES

- High Collector Current.(I_C= -500mA)
- Complementary To S8050.
- Excellent H_{FE} Linearity.



APPLICATIONS

High Collector Current.

ORDERING INFORMATION

Type No.	Marking	Package Code	
S8550	2TY	SOT-23	

MAXIMUM RATING @ Ta=25℃ unless otherwise specified

Symbol	Parameter	Value	Units
V _{CBO}	Collector-Base Voltage	-40	V
V _{CEO}	Collector-Emitter Voltage	-25	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-500	mA
P _C	Collector Dissipation	300	mW
T_{j}, T_{stg}	Junction and Storage Temperature	-55~150	$^{\circ}$

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Rev.A



Silicon Epitaxial Planar Transistor

S8550

ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μΑ,I _E =0	-40		V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA,I _B =0	-25		V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA,I _C =0	-5		V
Collector cut-off current	I _{CBO}	V _{CB} =-40V,I _E =0		-0.1	μΑ
Collector cut-off current	I _{CEO}	V _{CE} =-20V,I _B =0		-0.1	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} =-3V,I _C =0		-0.1	μΑ
DC authorit main	h _{FE}	V _{CE} =-1V,I _C =-50mA	120	350	
DC current gain		n _{FE}	V _{CE} =-1V,I _C =-500mA	50	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-500 mA, I _B = -50mA		-0.6	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-500 mA, I _B = -50mA		-1.2	V
Transition frequency	f⊤	V _{CE} =-6V, I _C = -20mA f=30MHz	150		MHz

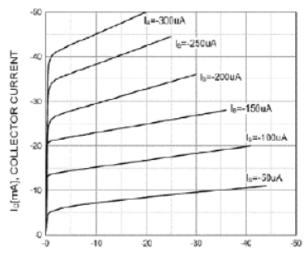
CLASSIFICATION OF $h_{FE(1)}$

Rank	L	Н
Range	120-200	200-350

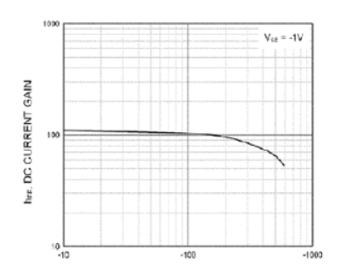
Silicon Epitaxial Planar Transistor

S8550

TYPICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

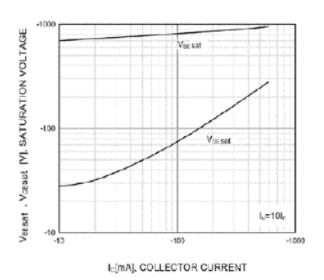


V_{CE}[V], COLLECTOR-EMITTER VOLTAGE



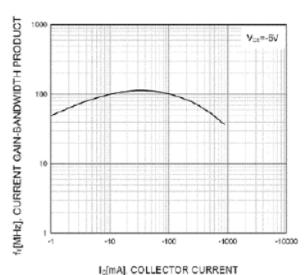
lo[mA], COLLECTOR CURRENT

Static Characteristic



Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage





Current Gain Bandwidth Product

BL Galaxy Electrical

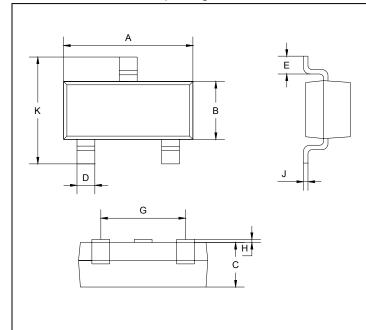
Silicon Epitaxial Planar Transistor

S8550

PACKAGE OUTLINE

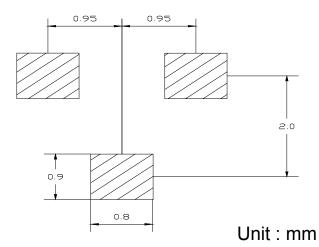
Plastic surface mounted package





SOT-23		
Dim	Min	Max
Α	2.85	2.95
В	1.25	1.35
С	1.0Typical	
D	0.37	0.43
E	0.35	0.48
G	1.85 1.95	
Н	0.02	0.1
J	0.1Typical	
K	2.35	2.45
All Dimensions in mm		

SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
S8550	SOT-23	3000/Tape&Reel